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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

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| Product Status | Obsolete |
|---------------------------------|---|
| Core Processor | PowerPC e500 |
| Number of Cores/Bus Width | 1 Core, 32-Bit |
| Speed | 1.0GHz |
| Co-Processors/DSP | Signal Processing; SPE, Security; SEC |
| RAM Controllers | DDR, DDR2, SDRAM |
| Graphics Acceleration | No |
| Display & Interface Controllers | - |
| Ethernet | 10/100/1000Mbps (4) |
| SATA | - |
| USB | - |
| Voltage - I/O | 1.8V, 2.5V, 3.3V |
| Operating Temperature | 0°C ~ 105°C (TA) |
| Security Features | Cryptography, Random Number Generator |
| Package / Case | 783-BBGA, FCBGA |
| Supplier Device Package | 783-FCPBGA (29x29) |
| Purchase URL | https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8548evtaqgd |
| | |

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Overview

- AESU-Advanced Encryption Standard unit
 - Implements the Rijndael symmetric key cipher
 - ECB, CBC, CTR, and CCM modes
 - 128-, 192-, and 256-bit key lengths
- AFEU—ARC four execution unit
 - Implements a stream cipher compatible with the RC4 algorithm
 - 40- to 128-bit programmable key
- MDEU—message digest execution unit
 - SHA with 160- or 256-bit message digest
 - MD5 with 128-bit message digest
 - HMAC with either algorithm
- KEU—Kasumi execution unit
 - Implements F8 algorithm for encryption and F9 algorithm for integrity checking
 - Also supports A5/3 and GEA-3 algorithms
- RNG—random number generator
- XOR engine for parity checking in RAID storage applications
- Dual I²C controllers
 - Two-wire interface
 - Multiple master support
 - Master or slave I^2C mode support
 - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
 - Optionally loads configuration data from serial ROM at reset via the I^2C interface
 - Can be used to initialize configuration registers and/or memory
 - Supports extended I²C addressing mode
 - Data integrity checked with preamble signature and CRC
- DUART
 - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
 - Programming model compatible with the original 16450 UART and the PC16550D
- Local bus controller (LBC)
 - Multiplexed 32-bit address and data bus operating at up to 133 MHz
 - Eight chip selects support eight external slaves
 - Up to eight-beat burst transfers
 - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller.
 - Three protocol engines available on a per chip select basis:
 - General-purpose chip select machine (GPCM)
 - Three user programmable machines (UPMs)

4.5 Platform to FIFO Restrictions

Note the following FIFO maximum speed restrictions based on platform speed.

For FIFO GMII mode:

FIFO TX/RX clock frequency \leq platform clock frequency/4.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency must be no more than 127 MHz.

For FIFO encoded mode:

FIFO TX/RX clock frequency \leq platform clock frequency/4.2

For example, if the platform frequency is 533 MHz, the FIFO TX/RX clock frequency must be no more than 167 MHz.

4.6 Platform Frequency Requirements for PCI-Express and Serial RapidIO

The CCB clock frequency must be considered for proper operation of the high-speed PCI-Express and Serial RapidIO interfaces as described below.

For proper PCI Express operation, the CCB clock frequency must be greater than:

See *MPC8548ERM*, *Rev.* 2, *PowerQUICC III Integrated Processor Family Reference Manual*, Section 18.1.3.2, "Link Width," for PCI Express interface width details.

For proper serial RapidIO operation, the CCB clock frequency must be greater than:

 $2 \times (0.80) \times (Serial RapidIO interface frequency) \times (Serial RapidIO link width)$

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See *MPC8548ERM*, *Rev.* 2, *PowerQUICC III Integrated Processor Family Reference Manual*, Section 17.4, "1x/4x LP-Serial Signal Descriptions," for serial RapidIO interface width and frequency details.

4.7 Other Input Clocks

For information on the input clocks of other functional blocks of the platform see the specific section of this document.

Figure 8 shows the GMII transmit AC timing diagram.



Figure 8. GMII Transmit AC Timing Diagram

8.2.2.2 GMII Receive AC Timing Specifications

This table provides the GMII receive AC timing specifications.

| Parameter/Condition | Symbol ¹ | Min | Тур | Max | Unit |
|---|-------------------------------------|-----|-----|-----|------|
| RX_CLK clock period | t _{GRX} | _ | 8.0 | _ | ns |
| RX_CLK duty cycle | t _{GRXH} /t _{GRX} | 35 | _ | 75 | ns |
| RXD[7:0], RX_DV, RX_ER setup time to RX_CLK | t _{GRDVKH} | 2.0 | _ | — | ns |
| RXD[7:0], RX_DV, RX_ER hold time to RX_CLK | t _{GRDXKH} | 0 | _ | — | ns |
| RX_CLK clock rise (20%-80%) | t _{GRXR} 2 | — | _ | 1.0 | ns |
| RX_CLK clock fall time (80%-20%) | t _{GRXF} 2 | — | | 1.0 | ns |

Notes:

1. The symbols used for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).}

2. Guaranteed by design.

Figure 9 provides the AC test load for eTSEC.



A timing diagram for TBI receive appears in Figure 16.



Figure 16. TBI Single-Clock Mode Receive AC Timing Diagram

8.2.6 RGMII and RTBI AC Timing Specifications

This table presents the RGMII and RTBI AC timing specifications.

| Parameter/Condition | Symbol ¹ | Min | Тур | Max | Unit |
|--|---------------------------------------|-------------------|-----|------------------|------|
| Data to clock output skew (at transmitter) | t _{SKRGT} 5 | -500 ⁶ | 0 | 500 ⁶ | ps |
| Data to clock input skew (at receiver) ² | t _{SKRGT} | 1.0 | _ | 2.8 | ns |
| Clock period ³ | t _{RGT} 5 | 7.2 | 8.0 | 8.8 | ns |
| Duty cycle for 10BASE-T and 100BASE-TX ^{3, 4} | t _{RGTH} /t _{RGT} 5 | 45 | 50 | 55 | % |
| Rise time (20%–80%) | t _{RGTR} 5 | _ | _ | 0.75 | ns |
| Fall time (20%–80%) | t _{RGTF} 5 | | — | 0.75 | ns |

Table 33. RGMII and RTBI AC Timing Specifications

Notes:

 In general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).

- 2. This implies that PC board design requires clocks to be routed such that an additional trace delay of greater than 1.5 ns is added to the associated clock signal.
- 3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns \pm 40 ns and 40 ns \pm 4 ns, respectively.
- 4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between.

5. Guaranteed by characterization.

6. In rev 1.0 silicon, due to errata, t_{SKRGT} is -650 ps (min) and 650 ps (max). See "eTSEC 10" in the device errata document.

9 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, RMII, TBI, and RTBI are specified in "Section 8, "Enhanced Three-Speed Ethernet (eTSEC)."

9.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in this table.

| Parameter | Symbol | Min | Мах | Unit |
|--|------------------|------|------------------------|------|
| Supply voltage (3.3 V) | OV _{DD} | 3.13 | 3.47 | V |
| Output high voltage ($OV_{DD} = Min, I_{OH} = -1.0 mA$) | V _{OH} | 2.10 | OV _{DD} + 0.3 | V |
| Output low voltage (OV _{DD} =Min, I _{OL} = 1.0 mA) | V _{OL} | GND | 0.50 | V |
| Input high voltage | V _{IH} | 2.0 | — | V |
| Input low voltage | V _{IL} | — | 0.90 | V |
| Input high current ($OV_{DD} = Max, V_{IN}^{1} = 2.1 V$) | I _{IH} | — | 40 | μA |
| Input low current ($OV_{DD} = Max, V_{IN} = 0.5 V$) | I _{IL} | -600 | — | μΑ |

Table 36. MII Management DC Electrical Characteristics

Note:

1. Note that the symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

9.2 MII Management AC Electrical Specifications

This table provides the MII management AC timing specifications.

Table 37. MII Management AC Timing Specifications

At recommended operating conditions with OV_{DD} is 3.3 V ± 5%.

| Parameter | Symbol ¹ | Min | Тур | Мах | Unit | Notes |
|----------------------------|---------------------|---------------------------------|-----|--|------|---------|
| MDC frequency | f _{MDC} | 0.72 | 2.5 | 8.3 | MHz | 2, 3, 4 |
| MDC period | t _{MDC} | 120.5 | | 1389 | ns | — |
| MDC clock pulse width high | t _{MDCH} | 32 | | — | ns | — |
| MDC to MDIO valid | t _{MDKHDV} | $16 \times t_{CCB}$ | | — | ns | 5 |
| MDC to MDIO delay | t _{MDKHDX} | (16 × t _{CCB} × 8) – 3 | | $(16 \times t_{\rm CCB} \times 8) + 3$ | ns | 5 |
| MDIO to MDC setup time | t _{MDDVKH} | 5 | | — | ns | — |
| MDIO to MDC hold time | t _{MDDXKH} | 0 | | — | ns | — |
| MDC rise time | t _{MDCR} | _ | _ | 10 | ns | 4 |

10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the device.

10.1 Local Bus DC Electrical Characteristics

This table provides the DC electrical characteristics for the local bus interface operating at $BV_{DD} = 3.3 \text{ V DC}$.

| Parameter | Symbol | Min | Мах | Unit |
|---|-----------------|------|------------------------|------|
| High-level input voltage | V _{IH} | 2 | BV _{DD} + 0.3 | V |
| Low-level input voltage | V _{IL} | -0.3 | 0.8 | V |
| Input current ($V_{IN}^{1} = 0 V \text{ or } V_{IN} = BV_{DD}$) | I _{IN} | _ | ±5 | μΑ |
| High-level output voltage ($BV_{DD} = min, I_{OH} = -2 mA$) | V _{OH} | 2.4 | — | V |
| Low-level output voltage (BV_{DD} = min, I_{OL} = 2 mA) | V _{OL} | _ | 0.4 | V |

Table 38. Local Bus DC Electrical Characteristics (3.3 V DC)

Note:

1. Note that the symbol V_{IN} , in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

Table 39 provides the DC electrical characteristics for the local bus interface operating at $BV_{DD} = 2.5 \text{ V DC}$.

Table 39. Local Bus DC Electrical Characteristics (2.5 V DC)

| Parameter | Symbol | Min | Max | Unit |
|---|-----------------|------|------------------------|------|
| High-level input voltage | V _{IH} | 1.70 | BV _{DD} + 0.3 | V |
| Low-level input voltage | V _{IL} | -0.3 | 0.7 | V |
| Input current $(V_{IN}^{1} = 0 V \text{ or } V_{IN} = BV_{DD})$ | I _{IH} | — | 10 | μA |
| | IIL | | -15 | |
| High-level output voltage ($BV_{DD} = min, I_{OH} = -1 mA$) | V _{OH} | 2.0 | — | V |
| Low-level output voltage ($BV_{DD} = min$, $I_{OL} = 1 mA$) | V _{OL} | — | 0.4 | V |

Note:

1. Note that the symbol V_{IN} , in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

PCI/PCI-X

Figure 36 shows the PCI/PCI-X input AC timing conditions.



Figure 36. PCI/PCI-X Input AC Timing Measurement Conditions

Figure 37 shows the PCI/PCI-X output AC timing conditions.





Table 53 provides the PCI-X AC timing specifications at 66 MHz.

| | Table 53 | . PCI-X AC | Timing | Specifications | at 66 | MHz |
|--|----------|------------|--------|-----------------------|-------|-----|
|--|----------|------------|--------|-----------------------|-------|-----|

| Parameter | Symbol | Min | Max | Unit | Notes |
|---|---------------------|-----|-----|--------|---------------|
| SYSCLK to signal valid delay | ^t PCKHOV | _ | 3.8 | ns | 1, 2, 3, 7, 8 |
| Output hold from SYSCLK | t _{PCKHOX} | 0.7 | | ns | 1, 10 |
| SYSCLK to output high impedance | t _{PCKHOZ} | - | 7 | ns | 1, 4, 8, 11 |
| Input setup time to SYSCLK | t _{PCIVKH} | 1.7 | _ | ns | 3, 5 |
| Input hold time from SYSCLK | t _{PCIXKH} | 0.5 | _ | ns | 10 |
| REQ64 to HRESET setup time | t _{PCRVRH} | 10 | _ | clocks | 11 |
| HRESET to REQ64 hold time | t _{PCRHRX} | 0 | 50 | ns | 11 |
| HRESET high to first FRAME assertion | t _{PCRHFV} | 10 | _ | clocks | 9, 11 |
| PCI-X initialization pattern to HRESET setup time | ^t PCIVRH | 10 | _ | clocks | 11 |

High-Speed Serial Interfaces (HSSI)

Figure 43 shows the SerDes reference clock connection reference circuits for HCSL type clock driver. It assumes that the DC levels of the clock driver chip is compatible with SerDes reference clock input's DC requirement.





Figure 44 shows the SerDes reference clock connection reference circuits for LVDS type clock driver. Since LVDS clock driver's common mode voltage is higher than the SerDes reference clock input's allowed range (100–400 mV), AC-coupled connection scheme must be used. It assumes the LVDS output driver features 50- Ω termination resistor. It also assumes that the LVDS transmitter establishes its own common mode level without relying on the receiver or other external component.



Figure 45 shows the SerDes reference clock connection reference circuits for LVPECL type clock driver. Since LVPECL driver's DC levels (both common mode voltages and output swing) are incompatible with the SerDes reference clock input's DC requirement, AC-coupling must be used. Figure 45 assumes that the LVPECL clock driver's output impedance is 50 Ω . R1 is used to DC-bias the LVPECL outputs prior

to AC-coupling. Its value could be ranged from 140 to 240 Ω depending on the clock driver vendor's requirement. R2 is used together with the SerDes reference clock receiver's 50- Ω termination resistor to attenuate the LVPECL output's differential peak level such that it meets the SerDes reference clock's differential input amplitude requirement (between 200 and 800 mV differential peak). For example, if the LVPECL output's differential peak is 900 mV and the desired SerDes reference clock input amplitude is selected as 600 mV, the attenuation factor is 0.67, which requires R2 = 25 Ω . Consult a clock driver chip manufacturer to verify whether this connection scheme is compatible with a particular clock driver chip.



Figure 45. AC-Coupled Differential Connection with LVPECL Clock Driver (Reference Only)

Figure 46 shows the SerDes reference clock connection reference circuits for a single-ended clock driver. It assumes the DC levels of the clock driver are compatible with the SerDes reference clock input's DC requirement.



Figure 46. Single-Ended Connection (Reference Only)

PCI Express

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

The reference impedance for return loss measurements is 50. to ground for both the D+ and D– line (that is, as measured by a vector network analyzer with 50- Ω probes—see Figure 50). Note that the series capacitors, CTX, are optional for the return loss measurement.



Figure 49. Minimum Receiver Eye Timing and Voltage Compliance Specification

17.5.1 Compliance Test and Measurement Load

The AC timing and voltage parameters must be verified at the measurement point, as specified within 0.2 inches of the package pins, into a test/measurement load shown in Figure 50.

NOTE

The allowance of the measurement point to be within 0.2 inches of the package pins is meant to acknowledge that package/board routing may benefit from D+ and D- not being exactly matched in length at the package pin boundary.



Figure 50. Compliance Test/Measurement Load

Serial RapidIO

| Characteristic | Symbol | Range | | Netos | |
|-----------------------------|---------------------|-------|------|--------|---|
| Characteristic | Symbol | Min | Max | Onit | NOICES |
| Output voltage | V _O | -0.40 | 2.30 | V | Voltage relative to COMMON of either signal comprising a differential pair |
| Differential output voltage | V _{DIFFPP} | 800 | 1600 | mVp-p | _ |
| Deterministic jitter | J _D | — | 0.17 | UI p-p | _ |
| Total jitter | J _T | — | 0.35 | UI p-p | _ |
| Multiple output skew | S _{MO} | — | 1000 | ps | Skew at the transmitter output between lanes of a multilane link |
| Unit interval | UI | 400 | 400 | ps | ±100 ppm |

Table 63. Long Run Transmitter AC Timing Specifications—2.5 GBaud

Table 64. Long Run Transmitter AC Timing Specifications—3.125 GBaud

| Characteristic | Symbol | Range | | Unit | Notas | |
|-----------------------------|---------------------|-------|---------|--------|---|--|
| | Symbol | Min | Min Max | | NOIES | |
| Output voltage | V _O | -0.40 | 2.30 | V | Voltage relative to COMMON of either signal comprising a differential pair | |
| Differential output voltage | V _{DIFFPP} | 800 | 1600 | mVp-p | _ | |
| Deterministic jitter | J _D | — | 0.17 | UI p-p | _ | |
| Total jitter | J _T | — | 0.35 | UI p-p | _ | |
| Multiple output skew | S _{MO} | _ | 1000 | ps | Skew at the transmitter output between lanes of a multilane link | |
| Unit interval | UI | 320 | 320 | ps | ±100 ppm | |

For each baud rate at which an LP-serial transmitter is specified to operate, the output eye pattern of the transmitter shall fall entirely within the unshaded portion of the transmitter output compliance mask shown in Figure 52 with the parameters specified in Table 65 when measured at the output pins of the device and the device is driving a $100-\Omega \pm 5\%$ differential resistive load. The output eye pattern of an LP-serial

19 Package Description

This section details package parameters, pin assignments, and dimensions.

19.1 Package Parameters

The package parameters for both the HiCTE FC-CBGA and FC-PBGA are provided in Table 70.

| Parameter | CBGA ¹ | PBGA ² |
|-------------------------|-------------------|-------------------|
| Package outline | 29 mm × 29 mm | 29 mm × 29 mm |
| Interconnects | 783 | 783 |
| Ball pitch | 1 mm | 1 mm |
| Ball diameter (typical) | 0.6 mm | 0.6 mm |
| Solder ball | 63% Sn | 63% Sn |
| | 37% Pb | 37% Pb |
| | 0% Ag | 0% Ag |
| Solder ball (lead-free) | 95% Sn | 96.5% Sn |
| | 4.5% Ag | 3.5% Ag |
| | 0.5% Cu | |

Table 70. Package Parameters

Notes:

1. The HiCTE FC-CBGA package is available on only Version 2.0 of the device.

2. The FC-PBGA package is available on only versions 2.1.1 and 2.1.2, and 3.0 of the device.

Package Description



- 1. All dimensions are in millimeters.
- 2. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 3. Maximum solder ball diameter measured parallel to datum A.
- 4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
- 5. Capacitors may not be present on all devices.
- 6. Caution must be taken not to short capacitors or exposed metal capacitor pads on package top.
- 7. Parallelism measurement shall exclude any effect of mark on top surface of package.
- 8. All dimensions are symmetric across the package center lines unless dimensioned otherwise.

Figure 56. Mechanical Dimensions and Bottom Surface Nomenclature of the FC-PBGA with Stamped Lid

Table 71. MPC8548E Pinout Listing (continued)

| Signal | Package Pin Number | Pin Type | Power Supply | Notes |
|--------------------------|---|----------|------------------|---------|
| MWE | E7 | 0 | GV _{DD} | — |
| MCAS | H7 | 0 | GV _{DD} | _ |
| MRAS | L8 | 0 | GV _{DD} | _ |
| MCKE[0:3] | F10, C10, J11, H11 | 0 | GV _{DD} | 11 |
| MCS[0:3] | K8, J8, G8, F8 | 0 | GV _{DD} | _ |
| MCK[0:5] | H9, B15, G2, M9, A14, F1 | 0 | GV _{DD} | — |
| MCK[0:5] | J9, A15, G1, L9, B14, F2 | 0 | GV _{DD} | — |
| MODT[0:3] | E6, K6, L7, M7 | 0 | GV _{DD} | — |
| MDIC[0:1] | A19, B19 | I/O | GV _{DD} | 36 |
| | Local Bus Controller Interface | | | • |
| LAD[0:31] | E27, B20, H19, F25, A20, C19, E28, J23, A25, K22, B28, D27, D19, J22, K20, D28, D25, B25, E22, F22, F21, C25, C22, B23, F20, A23, A22, E19, A21, D21, F19, B21 | I/O | BV _{DD} | _ |
| LDP[0:3] | K21, C28, B26, B22 | I/O | BV _{DD} | _ |
| LA[27] | H21 | 0 | BV _{DD} | 5, 9 |
| LA[28:31] | H20, A27, D26, A28 | 0 | BV _{DD} | 5, 7, 9 |
| LCS[0:4] | J25, C20, J24, G26, A26 | 0 | ΒV _{DD} | |
| LCS5/DMA_DREQ2 | D23 | I/O | BV _{DD} | 1 |
| LCS6/DMA_DACK2 | G20 | 0 | BV _{DD} | 1 |
| LCS7/DMA_DDONE2 | E21 | 0 | BV _{DD} | 1 |
| LWE0/LBS0/LSDDQM[0] | G25 | 0 | BV _{DD} | 5, 9 |
| LWE1/LBS1/LSDDQM[1] | C23 | 0 | BV _{DD} | 5, 9 |
| LWE2/LBS2/LSDDQM[2] | J21 | 0 | BV _{DD} | 5, 9 |
| LWE3/LBS3/LSDDQM[3] | A24 | 0 | BV _{DD} | 5, 9 |
| LALE | H24 | 0 | BV _{DD} | 5, 8, 9 |
| LBCTL | G27 | 0 | BV _{DD} | 5, 8, 9 |
| LGPL0/LSDA10 | F23 | 0 | BV _{DD} | 5, 9 |
| LGPL1/LSDWE | G22 | 0 | BV _{DD} | 5, 9 |
| LGPL2/LOE/LSDRAS | B27 | 0 | BV _{DD} | 5, 8, 9 |
| LGPL3/LSDCAS | F24 | 0 | BV _{DD} | 5, 9 |
| LGPL4/LGTA/LUPWAIT/LPBSE | H23 | I/O | BV _{DD} | |
| LGPL5 | E26 | 0 | BV _{DD} | 5, 9 |
| LCKE | E24 | 0 | BV _{DD} | _ |
| LCLK[0:2] | E23, D24, H22 | 0 | BV _{DD} | _ |

Table 74. MPC8543E Pinout Listing (continued)

| Signal | Package Pin Number | Pin Type | Power Supply | Notes |
|--------------------------|---|----------|------------------|---------|
| MWE | E7 | 0 | GV _{DD} | _ |
| MCAS | H7 | 0 | GV _{DD} | _ |
| MRAS | L8 | 0 | GV _{DD} | |
| MCKE[0:3] | F10, C10, J11, H11 | 0 | GV _{DD} | 11 |
| MCS[0:3] | K8, J8, G8, F8 | 0 | GV _{DD} | |
| MCK[0:5] | H9, B15, G2, M9, A14, F1 | 0 | GV _{DD} | _ |
| MCK[0:5] | J9, A15, G1, L9, B14, F2 | 0 | GV _{DD} | |
| MODT[0:3] | E6, K6, L7, M7 | 0 | GV _{DD} | _ |
| MDIC[0:1] | A19, B19 | I/O | GV _{DD} | 36 |
| | Local Bus Controller Interface | | | |
| LAD[0:31] | E27, B20, H19, F25, A20, C19, E28, J23, A25, K22, B28, D27, D19, J22, K20, D28, D25, B25, E22, F22, F21, C25, C22, B23, F20, A23, A22, E19, A21, D21, F19, B21 | I/O | BV _{DD} | |
| LDP[0:3] | K21, C28, B26, B22 | I/O | BV _{DD} | |
| LA[27] | H21 | 0 | BV _{DD} | 5, 9 |
| LA[28:31] | H20, A27, D26, A28 | 0 | BV _{DD} | 5, 7, 9 |
| LCS[0:4] | J25, C20, J24, G26, A26 | 0 | BV _{DD} | _ |
| LCS5/DMA_DREQ2 | D23 | I/O | BV _{DD} | 1 |
| LCS6/DMA_DACK2 | G20 | 0 | BV _{DD} | 1 |
| LCS7/DMA_DDONE2 | E21 | 0 | BV _{DD} | 1 |
| LWE0/LBS0/LSDDQM[0] | G25 | 0 | BV _{DD} | 5, 9 |
| LWE1/LBS1/LSDDQM[1] | C23 | 0 | BV _{DD} | 5, 9 |
| LWE2/LBS2/LSDDQM[2] | J21 | 0 | BV _{DD} | 5, 9 |
| LWE3/LBS3/LSDDQM[3] | A24 | 0 | BV _{DD} | 5, 9 |
| LALE | H24 | 0 | BV _{DD} | 5, 8, 9 |
| LBCTL | G27 | 0 | BV _{DD} | 5, 8, 9 |
| LGPL0/LSDA10 | F23 | 0 | BV _{DD} | 5, 9 |
| LGPL1/LSDWE | G22 | 0 | BV _{DD} | 5, 9 |
| LGPL2/LOE/LSDRAS | B27 | 0 | BV _{DD} | 5, 8, 9 |
| LGPL3/LSDCAS | F24 | 0 | BV _{DD} | 5, 9 |
| LGPL4/LGTA/LUPWAIT/LPBSE | H23 | I/O | BV _{DD} | |
| LGPL5 | E26 | 0 | BV _{DD} | 5, 9 |
| LCKE | E24 | 0 | BV _{DD} | |
| LCLK[0:2] | E23, D24, H22 | 0 | BV _{DD} | _ |

Package Description

| Signal | Package Pin Number | Pin Type | Power Supply | Notes |
|------------------|---|---|------------------|-------|
| TV _{DD} | W9, Y6 | Power for TSEC3 and TSEC4 (2,5 V, 3.3 V) | TV _{DD} | _ |
| GV _{DD} | B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13 | Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V,2.5 V) | GV _{DD} | _ |
| BV _{DD} | C21, C24, C27, E20, E25, G19, G23, H26, J20 | Power for local bus (1.8 V, 2.5 V, 3.3 V) | BV _{DD} | — |
| V _{DD} | M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19 | Power for core (1.1 V) | V _{DD} | _ |
| SV _{DD} | L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27 | Core power for SerDes transceivers (1.1 V) | SV _{DD} | _ |
| XV _{DD} | L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20 | Pad power for SerDes transceivers (1.1 V) | XV _{DD} | _ |
| AVDD_LBIU | J28 | Power for local bus PLL (1.1 V) | _ | 26 |
| AVDD_PCI1 | AH21 | Power for PCI1 PLL (1.1 V) | _ | 26 |
| AVDD_PCI2 | AH22 | Power for PCI2 PLL (1.1 V) | _ | 26 |
| AVDD_CORE | AH15 | Power for e500 PLL (1.1 V) | _ | 26 |
| AVDD_PLAT | AH19 | Power for CCB PLL (1.1 V) | | 26 |
| AVDD_SRDS | U25 | Power for SRDSPLL (1.1 V) | — | 26 |
| SENSEVDD | M14 | 0 | V _{DD} | 13 |

Table 74. MPC8543E Pinout Listing (continued)

| | Maximum Process | Unit | Notes | |
|------------------------|-----------------|------|-------|------|
| Characteristic | 800, 10 | | | |
| | Min | Мах | | |
| Memory bus clock speed | 166 | 200 | MHz | 1, 2 |

Table 80. Memory Bus Clocking Specifications (MPC8543E)

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 20.2, "CCB/SYSCLK PLL Ratio," and Section 20.3, "e500 Core PLL Ratio," for ratio settings.

2. The memory bus speed is half of the DDR/DDR2 data rate, hence, half of the platform clock frequency.

20.2 CCB/SYSCLK PLL Ratio

The CCB clock is the clock that drives the e500 core complex bus (CCB), and is also called the platform clock. The frequency of the CCB is set using the following reset signals, as shown in Table 81:

- SYSCLK input signal
- Binary value on LA[28:31] at power up

Note that there is no default for this PLL ratio; these signals must be pulled to the desired values. Also note that the DDR data rate is the determining factor in selecting the CCB bus frequency, since the CCB frequency must equal the DDR data rate.

For specifications on the PCI_CLK, see the PCI 2.2 Specification.

| Binary Value of LA[28:31] Signals | CCB:SYSCLK Ratio | Binary Value of LA[28:31] Signals | CCB:SYSCLK Ratio |
|-----------------------------------|------------------|-----------------------------------|------------------|
| 0000 | 16:1 | 1000 | 8:1 |
| 0001 | Reserved | 1001 | 9:1 |
| 0010 | 2:1 | 1010 | 10:1 |
| 0011 | 3:1 | 1011 | Reserved |
| 0100 | 4:1 | 1100 | 12:1 |
| 0101 | 5:1 | 1101 | 20:1 |
| 0110 | 6:1 | 1110 | Reserved |
| 0111 | Reserved | 1111 | Reserved |

Table 81. CCB Clock Ratio

21 Thermal

This section describes the thermal specifications of the device.

21.1 Thermal for Version 2.0 Silicon HiCTE FC-CBGA with Full Lid

This section describes the thermal specifications for the HiCTE FC-CBGA package for revision 2.0 silicon.

This table shows the package thermal characteristics.

| Characteristic | JEDEC Board | Symbol | Value | Unit | Notes |
|--|-------------------------|-----------------------|-------|------|-------|
| Die junction-to-ambient (natural convection) | Single-layer board (1s) | $R_{	extsf{	heta}JA}$ | 17 | °C/W | 1, 2 |
| Die junction-to-ambient (natural convection) | Four-layer board (2s2p) | $R_{	extsf{	heta}JA}$ | 12 | °C/W | 1, 2 |
| Die junction-to-ambient (200 ft/min) | Single-layer board (1s) | $R_{	extsf{	heta}JA}$ | 11 | °C/W | 1, 2 |
| Die junction-to-ambient (200 ft/min) | Four-layer board (2s2p) | $R_{	extsf{	heta}JA}$ | 8 | °C/W | 1, 2 |
| Die junction-to-board | N/A | R_{\thetaJB} | 3 | °C/W | 3 |
| Die junction-to-case | N/A | $R_{	extsf{	heta}JC}$ | 0.8 | °C/W | 4 |

Table 84. Package Thermal Characteristics for HiCTE FC-CBGA

Notes:

- 1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance.
- 2. Per JEDEC JESD51-6 with the board (JESD51-7) horizontal.
- 3. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- 4. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). The cold plate temperature is used for the case temperature, measured value includes the thermal resistance of the interface layer.

21.2 Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid

This section describes the thermal specifications for the FC-PBGA package for revision 2.1.1, 2.1.2, and 3.0 silicon.

This table shows the package thermal characteristics.

| Table 85. Package | Thermal | Characteristics | for FC-PBGA |
|-------------------|---------|-----------------|-------------|
|-------------------|---------|-----------------|-------------|

| Characteristic | JEDEC Board | Symbol | Value | Unit | Notes |
|--|-------------------------|-----------------------|-------|------|-------|
| Die junction-to-ambient (natural convection) | Single-layer board (1s) | $R_{	extsf{	heta}JA}$ | 18 | °C/W | 1, 2 |
| Die junction-to-ambient (natural convection) | Four-layer board (2s2p) | $R_{	extsf{	heta}JA}$ | 13 | °C/W | 1, 2 |
| Die junction-to-ambient (200 ft/min) | Single-layer board (1s) | $R_{	extsf{	heta}JA}$ | 13 | °C/W | 1, 2 |
| Die junction-to-ambient (200 ft/min) | Four-layer board (2s2p) | $R_{	extsf{	heta}JA}$ | 9 | °C/W | 1, 2 |

the ground plane. Use ceramic chip capacitors with the highest possible self-resonant frequency. All traces must be kept short, wide and direct.



1. An 0805 sized capacitor is recommended for system initial bring-up.

Figure 60. SerDes PLL Power Supply Filter

Note the following:

- AV_{DD}_SRDS must be a filtered version of SV_{DD}.
- Signals on the SerDes interface are fed from the XV_{DD} power plane.

22.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the device can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the device system, and the device itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD} , TV_{DD} , BV_{DD} , OV_{DD} , GV_{DD} , and LV_{DD} pin of the device. These decoupling capacitors must receive their power from separate V_{DD} , TV_{DD} , BV_{DD} , OV_{DD} , GV_{DD} , DV_{DD} , DV_{DD} , DV_{DD} , OV_{DD} , GV_{DD} , DV_{DD} , DV_{DD} , OV_{DD} , GV_{DD} , DV_{DD} , DV_{DD} , DV_{DD} , DV_{DD} , OV_{DD} , GV_{DD} , DV_{DD} , DV

These capacitors must have a value of 0.1 μ F. Only ceramic SMT (surface mount technology) capacitors must be used to minimize lead inductance, preferably 0402 or 0603 sizes. Besides, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD}, planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors must have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They must also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 μ F (AVX TPS tantalum or Sanyo OSCON). However, customers must work directly with their power regulator vendor for best values, types and quantity of bulk capacitors.

22.4 SerDes Block Power Supply Decoupling Recommendations

The SerDes block requires a clean, tightly regulated source of power (SV_{DD} and XV_{DD}) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors must be used to minimize inductance. Connections from all capacitors to power and ground must be done with multiple vias to further reduce inductance.

23.2 Part Marking

Parts are marked as the example shown in Figure 64.



Notes:

TWLYYWW is final test traceability code. MMMMM is 5 digit mask number. CCCCC is the country of assembly. This space is left blank if parts are assembled in the United States. YWWLAZ is assembly traceability code.

Figure 64. Part Marking for CBGA and PBGA Device